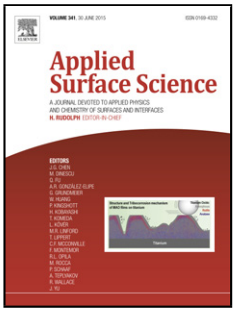

Title: A comparative study on the direct deposition of μc-Si:H and plasma-induced recrystallization of a-Si:H: Insight into Si crystallization in a high-density plasma

Authors: H.P. Zhou, M. Xu, S. Xu, Y.Y. Feng, L.X. Xu, D.Y. Wei, S.Q. Xiao

PII: S0169-4332(17)32936-7
DOI: https://doi.org/10.1016/j.apsusc.2017.10.013
Reference: APSUSC 37356

To appear in: *APSUSC*

Received date: 24-4-2017
Revised date: 25-9-2017
Accepted date: 2-10-2017

Please cite this article as: H.P.Zhou, M.Xu, S.Xu, Y.Y.Feng, L.X.Xu, D.Y.Wei, S.Q.Xiao, A comparative study on the direct deposition of μc-Si:H and plasma-induced recrystallization of a-Si:H: Insight into Si crystallization in a high-density plasma, Applied Surface Science https://doi.org/10.1016/j.apsusc.2017.10.013

A comparative study on the direct deposition of μc-Si:H and plasma-induced recrystallization of a-Si:H: Insight into Si crystallization in a high-density plasma

H. P. Zhou,[1,*] M. Xu,[2] S. Xu,[3,*] Y. Y. Feng,[1] L. X. Xu,[3] D. Y. Wei,[4] S. Q. Xiao[5]

[1]*School of Energy Science and Engineering, University of Electronic Science and Technology of China, 2006 Xiyuan Ave, West High-Tech Zone, Chengdu, Sichuan 611731, China*

[2]*Key Laboratory of Information Materials of Sichuan Province & School of Electrical and Information Engineering, Southwest University for Nationalities, Chengdu 610041, China*

[3]*Plasma Sources and Application Center, NIE, and Institute of Advanced Studies, Nanyang Technological University, 637616, Singapore*

[4] *School of Mechanical and Aerospace Engineering, Nanyang Technological University, 639798, Singapore*

[5]*Key Laboratory of Advanced Process Control for Light Industry (Ministry of Education), Department of Electronic Engineering, Jiangnan University, Wuxi 214122, China*

[*] Electronic-mail: haipzhou@uestc.edu.cn (H. P. Zhou), shuyan.xu@nie.edu.sg (S. Xu)

Graphical Abstract